



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Geoff W. Taylor et al.

Group Art Unit: 2811

Serial No.: 10/602,218

Examiner:

Filed: June 24, 2003

Attorney Docket: OPE-029

Title: Heterojunction Thyristor-based Amplifier

I hereby certify that this correspondence is being deposited on this day with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Alexandria, VA 22313-1450.

David P. Gordon Dec 12, 2003
David P. Gordon Date

Honorable Commissioner for Patents
Alexandria, VA 22313

SUBMITTAL OF DOCUMENTS PURSUANT TO DUTY OF DISCLOSURE

Pursuant to applicant's duty of disclosure 37 CFR Section 1.56, enclosed is a completed form PTOL-1449 as well as copies of the cited documents that relate to the above-referenced patent application. Since this document submittal is being presented prior to the first examination on the merits, no fee is due herewith.

The listed documents are brought to the Examiner's attention because they are known to the applicant and/or the applicant's attorney and may be considered by the Examiner to be material to his/her examination. This listing should not be construed as representation that a search has been made or that no better art exists. No inference should be made that the documents are in fact material merely because they are referenced herein. Moreover, no representation is made that the brief descriptions of the references herein necessarily describe the most material aspects of the references. Further, by this listing, the applicant is not making any admission regarding the relative dates of the invention and listed disclosures.

Respectfully submitted,

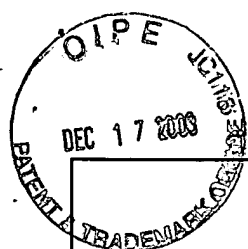
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INFORMATION DISCLOSURE CITATION

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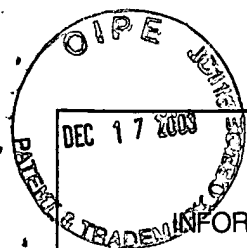
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10/602,218Applicant
Geoff Taylor et al.Filed
June 24, 2003Group
2811

US PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing date if approp.
	A	3,919,656	11/11/75	Sokal et al.	330	51	
	B	4,424,525	1/3/84	Mimura	357	23	
	C	4,658,403	4/14/87	Takiguchi et al.	372	96	
	D	4,683,484	7/28/87	Derkits, Jr.	357	16	
	E	4,806,997	2/21/89	Simmons et al.	357	16	
	F	4,814,774	3/21/89	Herczfeld	342	372	
	G	4,827,320	5/2/89	Morkoc et al.	357	22	
	H	4,829,272	5/9/89	Kameya	333	139	
	I	4,899,200	2/6/90	Shur et al.	357	30	
	J	4,949,350	8/14/90	Jewell et al.	372	45	
	K	5,010,374	4/23/91	Cooke et al.	357	16	
	L	5,105,248	4/14/92	Burke et al.	357	24	
	M	5,202,896	4/13/93	Taylor	372	50	
	N	5,337,328	8/9/94	Lang et al.	372	45	
	O	5,386,128	1/31/95	Fossum et al.	257	183.1	
	P	5,422,501	6/6/95	Bayraktaroglu	257	195	
	Q	5,436,759	7/25/95	Dijaili et al.	359	333	
	R	5,698,900	12/16/97	Bozada et al.	257	744	
	S	6,031,243	2/29/00	Taylor	257	13	
	T	6,043,519	3/28/00	Shealy et al.	257	195	
	U	US2002 /0067877A1	6/6/02	Braun et al.			
	V						
	W						

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INFORMATION DISCLOSURE CITATION PAGE 2 OF 2		Atty Docket No. OPE-029	Serial No. 10/602,218
		Applicant Geoff Taylor et al.	
		Filed June 24, 2003	Group 2811
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
AA	<u>10-Gb/s High-Speed Monolithically Integrated Photoreceiver Using InGaAs p-I-n PD and Planar Doped InAlAs/InGaAs HEMT's</u> by Y. Akahori et al., IEEE Photonics Technology Letters, Vol. 4, No. 7, July 1992		
BB	<u>10-Gbit/s InP-Based High-Performance Monolithic Photoreceivers Consisting of p-i-n Photodiodes and HEMT's</u> by Kiyoto Takahata et al., IEICE TRANS. ELECTRON., Vol. E83-C, No. 6, June 2000		
CC	<u>10 Ghz Bandwidth Monolithic p-i-n Modulation-Doped Field Effect Transistor Photoreceiver</u> by N.K. Dutta et al., Appl. Phys. Lett., Vol. 63, No. 15, 11 October 1993		
DD	<u>20 Gbit/s Long Wavelength Monolithic Integrated Photoreceiver Grown on GaAs</u> by V. Hurm et al., Electronic Letters, Vol. 33, No. 7, 27 March 1997		
EE	<u>Heterojunction Field-Effect Transistor (HFET)</u> by G.W. Taylor et al., Electronics Letters, Vol. 22, No. 15, pp. 784-786, 17 July 1986		
FF	<u>High Temperature Annealing of Modulation Doped GaAs/AlGaAs Heterostructures for FET Applications</u> by H. Lee et al., 1983 IEEE/Cornell Conf. On High-Speed Semiconductor Devices & Ckts, 8/83		
GG	<u>Monolithic Integrated Optoelectronic Circuits</u> by M. Berroth et al., 0-7803-2442-0-8/95 IEEE, 1995		
HH	<u>Physical Layer Solution for Very Short Reach Applications Utilizing Parallel Optics</u> by Steve Ahart, Agilent Technologies, ONIDS 2002		
II	<u>Parallel Optics: the Solution for High-Speed Interconnects</u> downloaded from www.paralleloptics.org, December 2000, updated April, May, July, Sept., Nov 2001 and Jan, April and July 2002		
JJ	<u>Submicrometre Gate Length Scaling of Inversion Channel Heterojunction Field Effect Transistor</u> by P.A. Kiely et al., Electronics Letters, Vol. 30, No. 6, 17 March 1994		
KK	<u>Theoretical and Experimental Results for the Inversion Channel Heterostructure Field Effect Transistor</u> by G.W. Taylor et al., IEE Proceedings-G, Vol 140, No. 6, December 1993		
EXAMINER		DATE CONSIDERED	